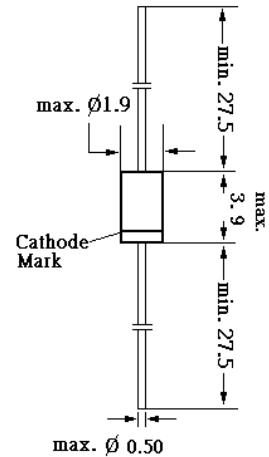


1SS106

SILICON SCHOTTKY BARRIER DIODE FOR VARIOUS DETECTOR High Speed Switching

Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal.



Glass case JEDEC DO-35

Dimensions in mm

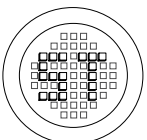
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Average Rectified Current	I_o	30	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{Stg}	-55 to +125	$^\circ\text{C}$

Characteristics at $T_{amb} = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Current at $V_F = 1\text{V}$	I_F	4.5	-	-	mA
Reverse current at $V_R = 6\text{V}$	I_R	-	-	70	μA
Capacitance at $V_R = 1\text{V}$, $f = 1\text{MHz}$	C	-	-	1.5	pF
Rectifier efficiency at $V_{in} = 2V_{rms}$, $f = 40\text{MHz}$, $R_L = 5\text{K}\Omega$, $C_L = 20\text{pF}$	η	70	-	-	%
ESD-Capability*1 at $C = 200\text{pF}$, Both forward and reverse direction 1 pulse	-	100	-	-	V

Note: 1. Failure criterion; $I_R/140\mu\text{A}$ at $V_R = 6\text{V}$



®

РАДИОТЕХ

Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru